AMENDMENTS TO THE CLAIMS

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1. (Original) A monomer of formula (lm):

$$P-Ar-N-Ar \begin{pmatrix} N-Ar \\ R \end{pmatrix} n$$
(Im)

wherein each Ar is the same or different and independently represents an optionally substituted phenyl or biphenyl; Ar¹ represents an optionally substituted phenyl or biphenyl; each P is the same or different and independently represents a leaving group capable of participating in metal insertion with a nickel or palladium complex catalyst; n is at least 2; and each R is a group of formula (II):

wherein G is hydrogen or a substituent selected from C_{1-20} alkyl; C_{1-20} alkoxy; C_{1-20} fluoroalkyl; C_{1-20} perfluoroalkyl; and fluorine.

- 2. (Original) A monomer according to claim 1 wherein each P is the same or different and is independently selected from halogen; a reactive boronic group selected from a boronic acid group, a boronic ester group and a borane group; a group of formula -B-Hal₃ M⁺ or DZ-B-Hal₃ wherein each Hal independently represents a halogen, M represents a metal cation and DZ represents diazonium; a group of formula wherein each Hal independently represents a halogen and M represents a metal cation a group of formula O-SIR⁷₃ wherein each R⁷ independently represents an optionally substituted alkyl or aryl; or a moiety of formula -O-SO₂-Z wherein Z is selected from the group consisting of optionally substituted alkyl and aryl.
- (Currently amended) A monomer according to claim 1 or 2 wherein n is 2 or 3. 3.

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4. (Original) A process for preparing a polymer comprising the step of polymerizing the monomer of formula (lm')

$$P-Ar-N-Ar \begin{pmatrix} N-Ar \\ R \end{pmatrix} n$$

$$(lm')$$

wherein each Ar is the same or different and independently represents an optionally substituted aryl or heteroaryl; Ar¹ represents an optionally substituted aryl or heteroaryl; each R is the same or different and independently represents a substitutent; each P is the same or different and independently represents a leaving group capable of participating in metal insertion with a nickel or palladium complex catalyst; and n is at least 2.

- 5. (Currently amended) A process according to claim 4 wherein each P is independently a halogen or a moiety of formula -O-SO₂-Z and the monomer of formula (lm) is polymerised polymerized in the presence of a nickel complex catalyst.
- 6. (Currently amended) A process according to claim 4 wherein each P is independently a halogen or a moiety of formula –O-SO₂-Z, the monomer of formula (lm) is polymerized with a second monomer having at least two reactive boron functional groups independently selected from a boronic acid group, a boronic ester group and a borane group, and the polymersation polymerization is performed in the presence of a palladium complex catalyst and a base.
- 7. (Currently amended) A process according to claim 4 wherein each P is independently a reactive boron functional group selected from a boronic acid group, a boronic ester group and a borane group; the monomer of formula (lm) is polymerised polymerized with a second monomer having at least two substitutents independently selected from halogen or a moiety of formula –O-SO₂-Z; and the polymerization polymerization is performed in the presence of a palladium complex catalyst and a base.
- 8. (Currently amended) A process according to claim 4 wherein one P is a halogen or a moiety of formula -O-SO₂-Z and the other P is a reactive boron functional group selected from a

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boronic acid group, a boronic ester group and a borane group, and the polymerisation polymerization is performed in the presence of a palladium complex catalyst and a base.

- 9. (Currently amended) A process according to any one of claims 4-8 claim 4 wherein the monomer of formula (lm) is polymerised polymerized with a second monomer selected from the group consisting of optionally substituted aryl and heteroaryl groups.
- 10. (Original) A process according to claim 9 wherein the second monomer is selected from the group consisting of optionally substituted phenyl, fluorene, spirobifluorene, indenofluorene and heteroaryl.
- (Original) A co-polymer comprising a first repeat unit of formula (lr) and a second 11. repeat unit Ar²:

$$\begin{array}{c}
-Ar-N-Ar^{1} \left(N-Ar \right) \\
R & R
\end{array}$$
(Ir)

wherein each Ar is the same or different and independently represents an optionally substituted aryl or heteroaryl; Ar¹ represents an optionally substituted aryl or heteroaryl; each R is the same or different and independently represents a substitutent; n is at least 2; and Ar² represents an optionally substituted aryl or heteroaryl that has a backbone consisting of aryl or heteroaryl groups and that is directly linked and conjugated to Ar of the first repeat unit of formula (lr).

- 12. (Original) A co-polymer according to claim 11 wherein Ar2 is selected from the group consisting of optionally substituted phenyl, fluorene, spirobifluorene, indenofluorene and heteroraryl.
- (Currently amended) An optical device comprising a first electrode for injection of 13. charge carriers of a first type, a second electrode for injection of charge carriers of a second type and a polymer according to claim 11 or 12 located between the first and second electrodes.
- (Currently amended) A method of forming an optical device comprising 14. - 5 -429663

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- depositing from solution a polymer according to claim 11 or 12 onto a substrate carrying a first electrode for injection of charge carriers of a first type, and

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- depositing over the polymer a second electrode for injection of charge carriers of a second type.
- 15. (Currently amended) A switching device comprising a polymer according to claim 11 or 12.
- 16. (Currently amended) A field effect transistor comprising, in sequence, a gate electrode; an insulator; a polymer according to claim 11 or 12; and a drain electrode and a source electrode on the polymer.
- 17. (Original) An integrated circuit comprising a field effect transistor according to claim 16.

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